

AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

LISTING OF CLAIMS:

1.-158. (Cancelled).

159. (New) A metal-polishing liquid material comprising an oxidized-metal etchant, a protective film-forming agent, and a dissolution promoter for the protective film-forming agent, wherein the dissolution promoter is a surfactant, said surfactant being at least one selected from the group consisting of esters, ethers, polysaccharides, salts of amino acids, polycarboxylic acids, salts of polycarboxylic acids, vinyl polymers, sulfonic acids, sulfonates, and amides.

160. (New) The metal-polishing liquid material according to claim 159, further comprising at least one of an oxidizing agent and water.

161. (New) The metal-polishing liquid material according to claim 159, comprising the ingredient group consisting of the oxidizing agent, the oxidized-metal etchant, the protective film-forming agent and the dissolution promoter in a divided state into two constituent elements not mixed.

162. (New) The metal-polishing liquid material according to claim 160, wherein at least a part of the protective film-forming agent is solid, having a mean particle size of at most 100 μm .

163. (New) The metal-polishing liquid material according to claim 160, further comprising abrasive grains.

164. (New) A metal-polishing liquid which comprises an oxidizing agent, an oxidized-metal etchant, a protective film-forming agent, a dissolution promoter for the protective film-forming agent, and water, wherein the dissolution promoter is a surfactant, said surfactant being at least one selected from the group consisting of esters, ethers, polysaccharides, salts of amino acids, polycarboxylic acids, salts of polycarboxylic acids, vinyl polymers, sulfonic acids, sulfonates, and amides.

165. (New) The metal-polishing liquid according to claim 164, wherein at least a part of the protective film-forming agent is solid, having a mean particle size of at most 100 μm .

166. (New) The metal-polishing liquid according to claim 164, further comprising abrasive grains.

167. (New) A method for producing a metal-polishing liquid, comprising a step of diluting the metal-polishing liquid material of claim 160 with a diluent.

168. (New) A method for producing a metal-polishing liquid of claim 164, comprising a step of diluting a metal-polishing liquid material comprising at least one ingredient of an ingredient group consisting of the oxidizing agent, the oxidized-metal etchant, the protective film-forming agent and the dissolution promoter for the protective film-forming agent, with an aqueous solution for dilution of at least one

ingredient of the ingredient group.

169. (New) A method for producing a metal-polishing liquid of claim 164, which comprises a step of mixing the following in any desired order:

a first constituent element that contains at least one ingredient of an ingredient group consisting of said oxidizing agent, said oxidized-metal etchant, said protective film-forming agent and said dissolution promoter for the protective film-forming agent,

a second constituent element that contains at least one of the other ingredients of the ingredient group, and

a diluent,

wherein at least one of the first constituent element and the second constituent element includes said dissolution promoter for the protective film-forming agent.

170. (New) The method for producing a metal-polishing liquid according to claim 169, wherein the diluent is water or an aqueous diluent solution.

171. (New) The method for producing a metal-polishing liquid according to claim 169, wherein the first constituent element comprises the oxidizing agent, and the second constituent element comprises the oxidized-metal etchant, the protective film-forming agent and the dissolution promoter.

172. (New) The method for producing a metal-polishing liquid according to claim 169, wherein the first constituent element further comprises the protective film-

forming agent and the dissolution promoter.

173. (New) The method for producing a metal-polishing liquid as claimed in claim 169, wherein in the mixing step, the oxidizing agent and the oxidizing agent-containing mixture are kept at a temperature of at most 40°C.

174. (New) The method for producing a metal-polishing liquid as claimed in claim 169, wherein at least a part of the protective film-forming agent is solid, having a mean particle size of at most 100 μm , and is dissolved or dispersed in the metal-polishing liquid in the mixing step.

175. (New) A polishing method comprising a polishing step of;
applying the metal-polishing liquid of claim 164 to a polishing pad set on a platen, and
polishing the surface of an article to be polished with the polishing pad by moving the polishing pad and the surface of the article relatively to each other while keeping the surface of the article in contact with the polishing pad.

176. (New) The polishing method according to claim 175, further comprising a step of mixing the constituent elements of the metal-polishing liquid to prepare the metal-polishing liquid, prior to the polishing step,

wherein; the mixing step is for mixing the following:

a first constituent element that contains at least one ingredient of an ingredient group consisting of the oxidizing agent, the oxidized-metal etchant, the protective film-forming agent and the dissolution promoter for the protective film-

forming agent,

a second constituent element that contains at least one of the other ingredients of the ingredient group, and

a diluent,

in any desired order.

177. (New) The metal-polishing liquid material according to claim 159, wherein at least a part of the protective film-forming agent is solid, having a mean particle size of at most 100 μm .

178. (New) The metal-polishing liquid material according to claim 159, further comprising abrasive grains.

179. (New) A method for producing a metal-polishing liquid, comprising a step of diluting the metal-polishing liquid material of claim 159 with a diluent.

180. (New) The method for producing a metal-polishing liquid according to claim 167, wherein the diluent is water or an aqueous diluent solution.

181. (New) The metal-polishing liquid material according to claim 159, wherein said dissolution promoter promotes dissolving of the protective film-forming agent in water.

182. (New) The metal-polishing liquid material according to claim 161, wherein each ingredient of said ingredient group is a different ingredient.

183. (New) The metal-polishing liquid material according to claim 160, wherein the protective film-forming agent, the dissolution promoter, the oxidized-metal etchant, the oxidizing agent and water are different ingredients.

184. (New) The metal-polishing liquid material according to claim 159, wherein the protective film-forming agent is at least one selected from the group consisting of ammonia, amines, amino acids, imines, azoles, mercaptans, polysaccharides, salts of amino acids, polycarboxylic acids and their salts, and vinyl polymers.

185. (New) The metal-polishing liquid according to claim 164, wherein the protective film-forming agent is at least one selected from the group consisting of ammonia, amines, amino acids, imines, azoles, mercaptans, polysaccharides, salts of amino acids, polycarboxylic acids and their salts, and vinyl polymers.